

L Number	Hits	Search Text	DB	Time stamp
1	891	((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:03
2	67	((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and ((single adj crystalline) with semiconductor)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:32
3	67	((((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and ((single adj crystalline) with semiconductor)) and substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:04
4	52	((((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and ((single adj crystalline) with semiconductor)) and (bipolar with substrate)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:04
5	25	("4008111" "4571818" "4601779" "4649627" "4893509" "4910165" "4985745" "5004705" "5086011" "5143862" "5234535" "5258318" "5294823" "5321298" "5352912" "5481126" "5496745" "5516718" "5543653" "5627092" "5656514" "5770484" "5789793" "5895953" "5956597").PN.	USPAT	2004/10/04 09:17
6	4	("5399507" "5529947" "5573972" "5726089").PN.	USPAT	2004/10/04 09:19
7	5	5573972.URPN.	USPAT	2004/10/04 09:28
8	159	SOI and bulk and ((single adj crystalline) with semiconductor)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:33
9	57	(SOI and bulk and ((single adj crystalline) with semiconductor)) and bipolar	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:37
10	1792	257/347.cccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:50
11	391	257/349.cccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:52
12	860	257/370.cccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 10:12
13	668	257/378.cccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 10:12
-	2	("6724045").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 18:48
-	9	("5102809" "5212397" "5258318" "5294823" "5371401" "5430318" "5909626" "6096584" "6232649").PN.	USPAT	2004/06/26 18:27
-	1897	bicmos.ab.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 18:49

	37	bicmos.ab. and MOS and bipolar and (buried with insulat\$4)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 18:54
-	153	(element adj isolation) and MOS and bipolar and (buried with insulat\$4)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 18:55
-	96	((element adj isolation) and MOS and bipolar and (buried with insulat\$4)) and ((bipolar adj transistor) and (MOS adj transistor))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 19:03
-	10	((element adj isolation) and MOS and bipolar and (buried with insulat\$4)) and ((bipolar adj transistor) and (MOS adj transistor)).ab.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 19:04
-	5	("5356827" "5476809" "5529947" "5573972" "5688702").PN.	USPAT	2004/06/26 19:07
-	6	5688702.URPN.	USPAT	2004/06/26 19:17
-	24	("4139442" "4467344" "4587545" "4602268" "4608590" "4754310" "4916085" "5057895" "5171699" "5181095" "5216275" "5336634" "5466963" "5467347" "5479498" "5512774" "5554872" "5683075" "5688702" "5841197" "5856700" "5872044" "5914280" "5939755").PN.	USPAT	2004/06/26 19:18
-	5	CMOS and bipolar and (CMOS with (buried adj insulat\$4)) and (CMOS and bipolar).ab.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 19:27
-	0	CMOS and bipolar and (CMOS with (buried adj insulat\$4)) and (element adj isolation)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 19:28
-	347	CMOS and bipolar and (element adj isolation)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 19:29
-	70	(CMOS and bipolar and (element adj isolation)) and (BOX or (buried adj oxide) or (buried adj insulat\$4))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 19:30
-	857	((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:02
-	183	((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and bipolar.ab.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 19:31
-	15	((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and bipolar.ab.) and (element adj isolation)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 20:07
-	191	((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and bicmos	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 19:37
-	67	((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and bicmos) and ((element or trench) adj isolation)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 19:38
-	8	("4038680" "4089021" "4780430" "5023194" "5065213" "5118635" "5344785" "5716887").PN.	USPAT	2004/06/26 19:40
-	4	("5100810" "5102809" "5593915" "5952695").PN.	USPAT	2004/06/26 19:44

-	35	5100810.URPN.	USPAT	2004/06/26 19:46
-	22	("3913124" "4700461" "4769687" "4839309" "4884117" "4965872" "5028557" "5049513" "5057580" "5060035" "5072274" "5073506" "5075241" "5100810" "5102809" "5140390" "5162882" "5212397" "5241211" "5273915" "5289027" "5621239").PN.	USPAT	2004/06/26 19:54
-	35	5100810.URPN.	USPAT	2004/06/26 19:58
-	975	((CMOS or MOS) with transistor) and ((bipolar or NPN or PNP) with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 20:03
-	131	((CMOS or MOS) with transistor) and ((bipolar or NPN or PNP) with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and ((CMOS or MOS) with ((BOX or (buried adj oxide) or (buried adj insulat\$4))))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 20:06
-	17	((CMOS or MOS) with transistor) and ((bipolar or NPN or PNP) with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and ((CMOS or MOS) with ((BOX or (buried adj oxide) or (buried adj insulat\$4)))) and (element adj isolation)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 20:07